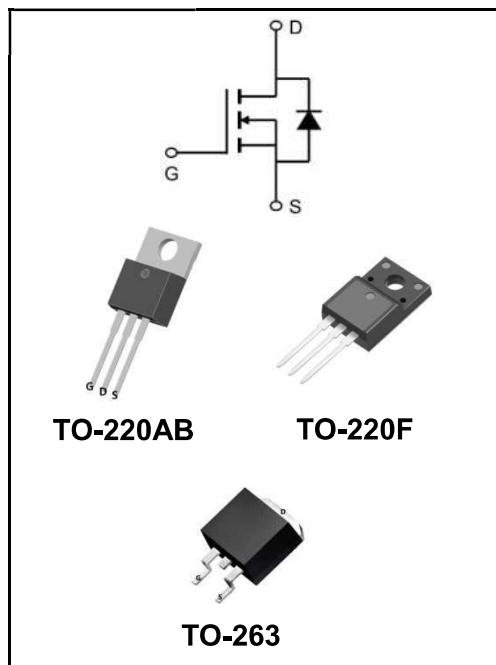


100V N-CHANNEL ENHANCEMENT MODE MOSFET
MAIN CHARACTERISTICS

I_D	55A
V_{DSS}	100V
$R_{DS(on)-typ}(@V_{GS}=10V)$	< 21mΩ (Type: 15 mΩ)


Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply

Product Specification Classification

Part Number	Package	Marking	Pack
YFW55N10AT	TO-220AB	YFW 55N10AT XXXXX	1000PCS/Box
YFW55N10AF	TO-220F	YFW 55N10AF XXXXX	1000PCS/Box
YFW55N10AS	TO-263	YFW 55N10AS XXXXX	800PCS/Reel

Maximum Ratings at $T_c=25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	100	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_c=25^\circ\text{C}$	I_D	55	A
Pulsed drain current ²⁾ , $T_c=25^\circ\text{C}$	$I_{D, \text{pulse}}$	110	A
Power dissipation ³⁾ , $T_c=25^\circ\text{C}$	P_D	50	W
Single Pulse Avalanche Energy ⁵⁾	E_{AS}	57	mJ
Operation and storage temperature	T_{STG}, T_J	-55 to +150	°C

Maximum Ratings at T_c=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	BV _{DSS}	100	-	-	V
Gate -Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	V _{GS(th)}	1.4	-	2.5	V
Drain-source on-state resistance	V _{GS} =10V, I _D =10A	R _{DS(ON)}	-	15	21	mΩ
	V _{GS} =4.5V, I _D =7A		-	20	26	
Gate-Source Leakage Current	V _{GS} =20V	I _{GSS}	-	-	100	nA
	V _{GS} =-20V		-	-	-100	
Drain-Source Leakage Current	V _{DS} =100V , V _{GS} =0V	I _{DSS}	-	-	1	μA
Input Capacitance	V _{GS} =0V V _{DS} =50V f=100KHz	C _{iss}	-	1003.9	-	pF
Output Capacitance		C _{oss}	-	185.4	-	
Reverse Transfer Capacitance		C _{rss}	-	9.8	-	
Turn-on delay time	V _{GS} =10V V _{DS} =50V R _G =10Ω I _D =5A	t _{d(on)}	-	16.6	-	ns
Rise Time		T _r	-	3.8	-	
Turn-Off Delay Time		t _{d(OFF)}	-	75.5	-	
Fall Time		t _f	-	46	-	
Total Gate Charge	I _D =5A V _{DS} =50V V _{GS} =10V	Q _g	-	16.2	-	nC
Gate-Source Charge		Q _{gs}	-	2.8	-	
Gate-Drain Charge		Q _{gd}	-	4.1	-	
Gate plateau voltage		V _{plateau}	-	3	-	
Diode forward current	V _{GS} <V _{th}	I _s	-	-	16	A
Pulsed Source Current		I _{SP}	-	-	48	
Diode Forward Voltage	I _s = ¹²³⁴ A, V _{GS} =0 V	V _{SD}	-	-	1.3	V
Reverse Recovery Time	I _s =5A , dI/dt=100A/μs	t _{rr}	-	49	-	ns
Reverse Recovery Charge		Q _{rr}	-	61.8	-	nC
Peak reverse recovery current		I _{rrm}	-	2.4	-	A

1) Calculated continuous current based on maximum allowable junction temperature.

2) Repetitive rating; pulse width limited by max. junction temperature.

3) Pd is based on max. junction temperature, using junction-case thermal resistance.

4) The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.

5) V_{DD}=50 V, R_G=50 Ω, L=0.3 mH, starting T_j=25 °C.

Ratings and Characteristic Curves

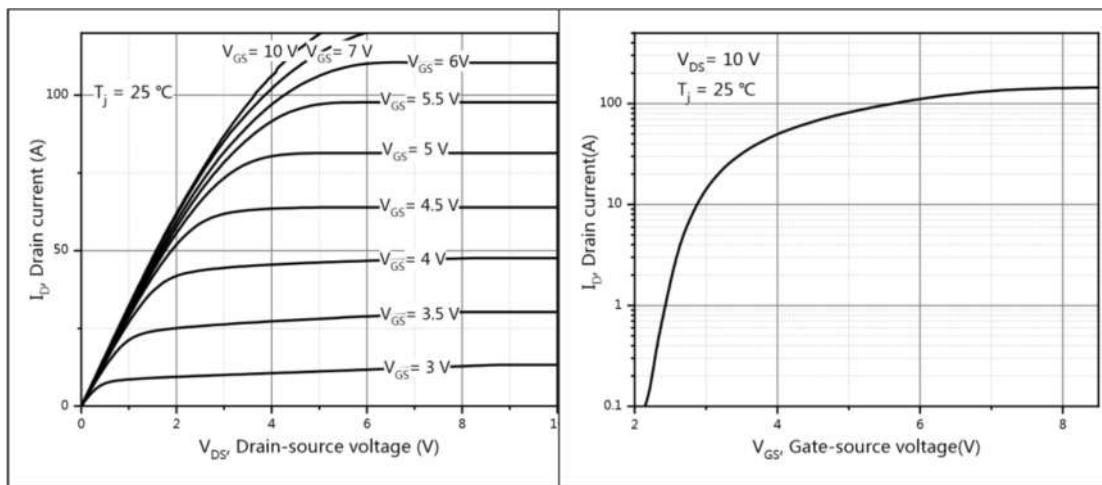


Figure 1, Typ. output characteristics

Figure 2, Typ. transfer characteristics

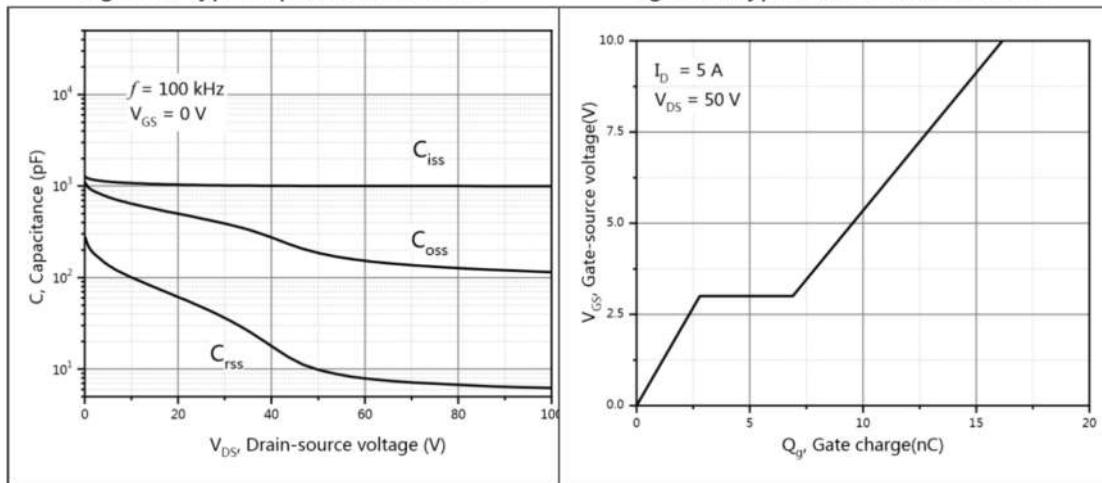


Figure 3, Typ. capacitances

Figure 4, Typ. gate charge

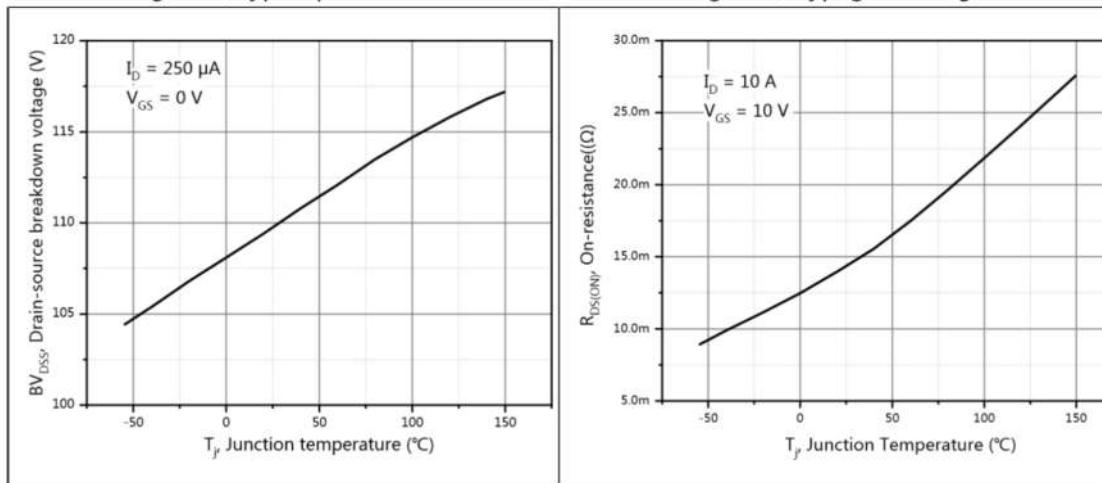


Figure 5, Drain-source breakdown voltage

Figure 6, Drain-source on-state resistance

Ratings and Characteristic Curves

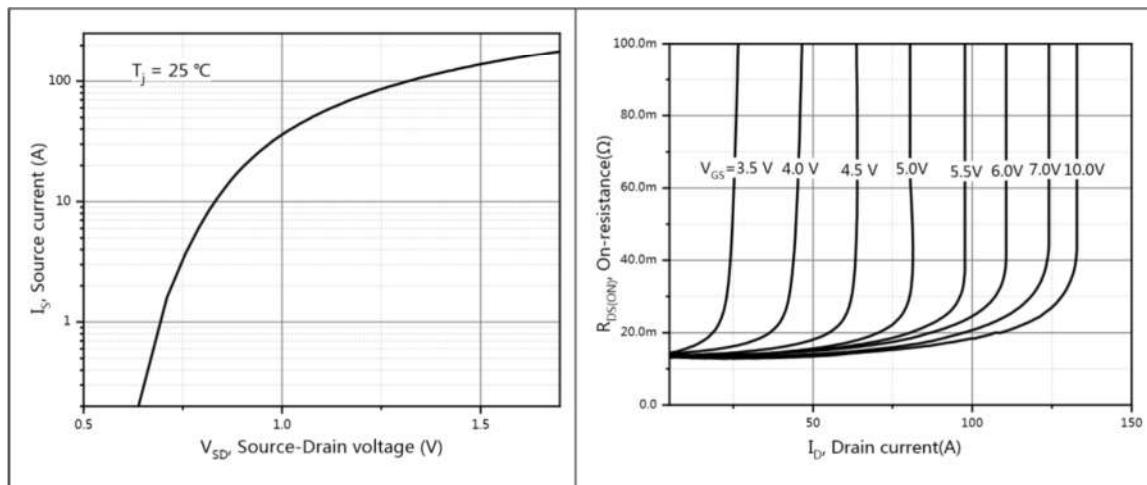


Figure 7, Forward characteristic of body diode

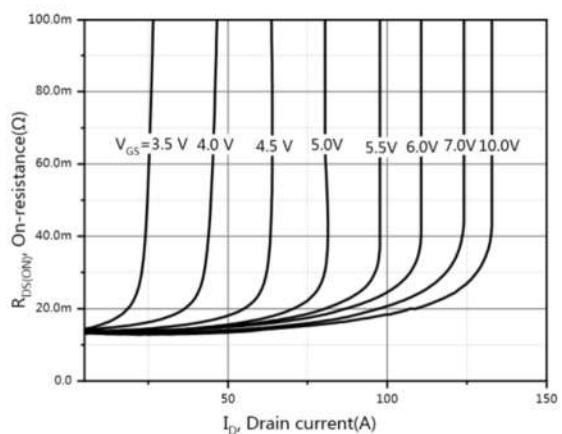


Figure 8, Drain-source on-state resistance

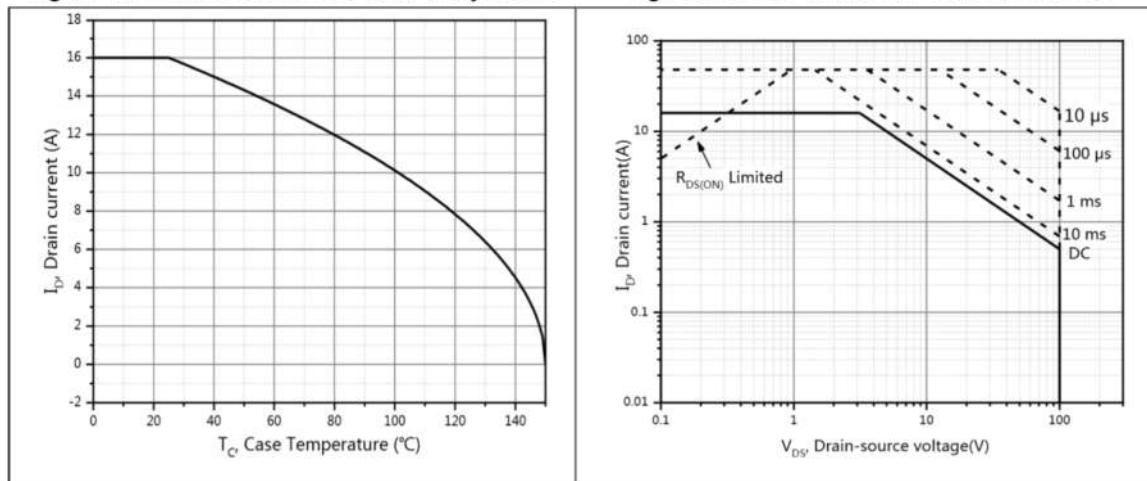


Figure 9, Drain current

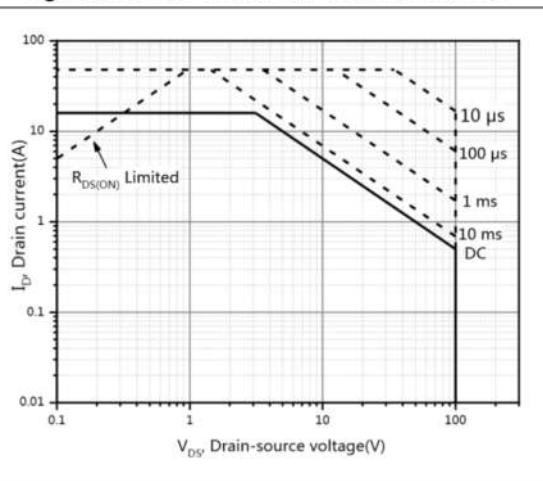
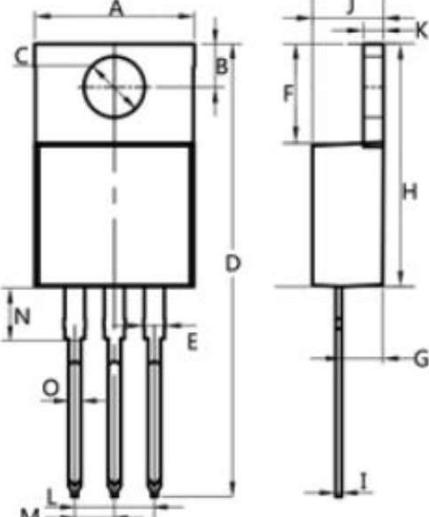


Figure 10, Safe operation area $T_C=25^\circ\text{C}$

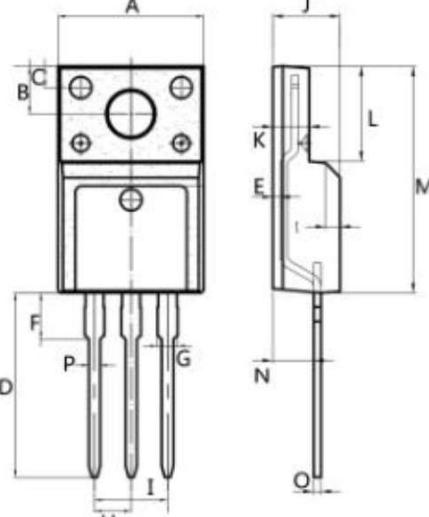
Package Outline Dimensions Millimeters

TO-220AB



Dim.	Min.	Max.
A	10.15	10.35
B	2.65	2.95
C	3.70	3.90
D	28.5	29.5
E	1.30	1.45
F	6.35	6.55
G	2.9	3.3
H	15.0	16.0
I	0.38	0.42
J	4.45	4.55
K	1.25	1.35
L	Typ 5.08	
M	Typ 2.54	
N	3.1	3.3
O	0.76	0.84
All Dimensions in millimeter		

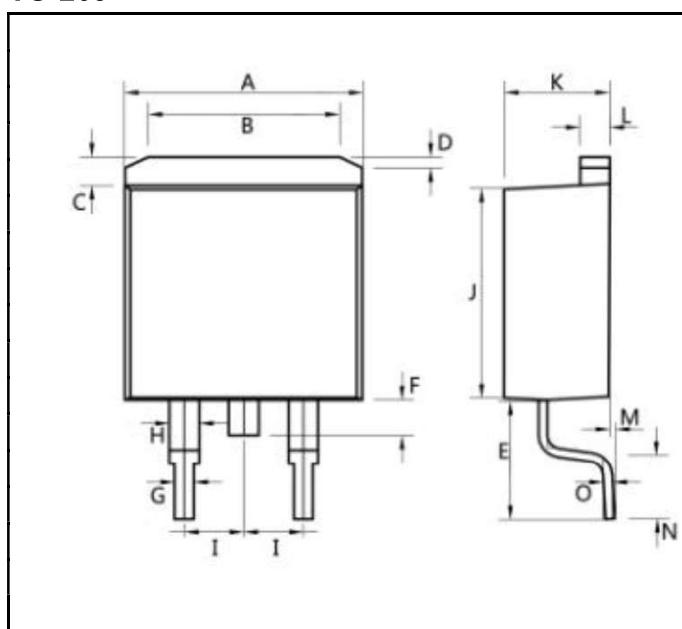
TO-220F



Dim.	Min.	Max.
A	9.95	10.25
B	2.95	3.25
C	1.25	1.45
D	12.95	13.25
E	0.50	0.65
F	3.1	3.3
G	1.30	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.60	4.75
K	2.50	2.65
L	6.35	6.55
M	15.4	16.0
N	2.75	3.05
O	0.48	0.52
P	0.76	0.84
All Dimensions in millimeter		

Package Outline Dimensions Millimeters

TO-263



The diagram illustrates the TO-263 package outline with two views: a top view showing the lead configuration and a side view showing the profile. Dimension labels include: A (width), B (width), C (height), D (lead thickness), E (lead height), F (lead pitch), G (lead thickness), H (lead height), I (lead pitch), J (total height), K (width), L (lead thickness), M (lead thickness), N (lead pitch), and O (lead thickness). The side view also shows the lead profile with dimensions E, M, and O.

Dim.	Min.	Max.
A	10.1	10.2
B	7.4	7.6
C	1.3	1.5
D	0.55	0.75
E	5.0	6.0
F	1.4	1.6
G	0.78	0.86
H	1.2	1.3
I	Typ2.54	
J	8.4	8.6
K	4.45	4.55
L	1.25	1.35
M	0.02	0.1
N	2.4	2.8
O	0.36	0.40

All Dimensions in millimeter